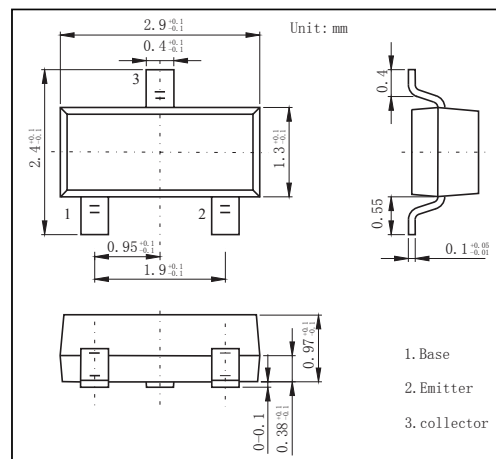


SOT-23 Plastic-Encapsulate Transistors
FEATURES

- Low Cob.Cob=2.0pF (Typ.)
- NPN Transistors

MECHANICAL DATA

- Case style:SOT-23molded plastic
- Mounting position:any


MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	60	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	7	V
Collector current	I_C	0.15	A
Collector power dissipation	P_C	0.2	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	- 5 5 t o + 1 5 0	°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_C = 50 \mu A, I_E = 0$	60			V
Collector- emitter breakdown voltage	V_{CEO}	$I_C = 1 mA, I_B = 0$	50			
Emitter - base breakdown voltage	V_{EBO}	$I_E = 50 \mu A, I_C = 0$	7			
Collector-base cut-off current	I_{CBO}	$V_{CB} = 60 V, I_E = 0$			100	nA
Emitter cut-off current	I_{EBO}	$V_{EB} = 7 V, I_C = 0$			100	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 50 mA, I_B = 5 mA$			0.4	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = 50 mA, I_B = 5 mA$			1.2	
DC current gain	h_{FE}	$V_{CE} = 6 V, I_C = 1 mA$	120		560	
Collector output capacitance	C_{ob}	$V_{CB} = 12 V, I_E = 0, f = 1 MHz$		2	3.5	pF
Transition frequency	f_T	$V_{CE} = 12 V, I_E = -2 mA, f = 100 MHz$	80			MHz

RATINGS AND CHARACTERISTIC CURVES

